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Sommario/riassunto	A comprehensive introduction and up-to-date reference to SiC power semiconductor devices covering topics from material properties to applications Based on a number of breakthroughs in SiC material science and fabrication technology in the 1980's and 1990's, the first SiC Schottky barrier diodes (SBDs) were released as commercial products in 2001. The SiC SBD market has grown significantly since that time, and SBDs are now used in a variety of power systems, particularly switch-mode power supplies and motor controls. SiC power MOSFET's entered commercial production in 2011, providing rugged, high